

control unit;

a second electrode for receiving the first predetermined voltage, a second predetermined voltage, and a third predetermined voltage to adjust charges stored in the parasitic capacitor so that corresponding data represented by amounts of the charges are stored; and

a third electrode electrically connected to the parasitic capacitor.

[c6] 6. The control method of claim 5 wherein the first predetermined voltage is less than the second predetermined voltage but greater than the third predetermined voltage.

[c7] 7. The control method of claim 6 wherein the second predetermined voltage stands for a binary value "1", and the third predetermined voltage stands for a binary value "0".

[c8] 8. The control method of claim 7 further comprising adjusting a voltage level of the third electrode to approach the second predetermined voltage or the third predetermined voltage according to amounts of charges stored on the floating gate.

[c9] 9. The control method of claim 8 further comprising:
passing an input voltage to the control gate of each memory cell for inducing the conductive channel on the surface of the substrate of each memory cell so as to force the parasitic capacitor of each memory cell to approach a predetermined capacitance.

[c10] 10. The control method of claim 1 further comprising adjusting amounts of charges stored on the floating gate to record the corresponding data according to the voltage shift.

[c11] 11. The control method of claim 10 further comprising:
adjusting amounts of the charges stored on the floating gate to be greater than a predetermined storage number if the voltage shift is positive; and
adjusting amounts of the charges stored on the floating gate to be less than the predetermined storage number if the voltage shift is negative.